

2N5949 N-Channel JFET

Features

- InterFET [N0032H Geometry](#)
- Low Noise: 7 nV/VHz Typical
- Low Ciss: 6pF Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

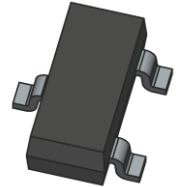
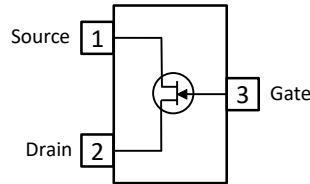
Applications

- Audio Amplifiers
- General Purpose Amplifiers
- Switches

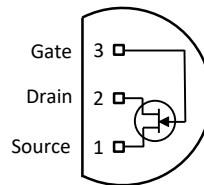
Description

The -30V InterFET 2N5949 JFET is targeted for low noise switching and audio amplifier applications. Gate leakages are typically less than 10pA at room temperatures.

SOT23 Top View



TO-92 Bottom View



Product Summary

Parameters		2N5949 Min	Unit
BV _{GSS}	Gate to Source Breakdown Voltage	30	V
I _{DSS}	Drain to Source Saturation Current	12	mA
V _{GS(off)}	Gate to Source Cutoff Voltage	3	V
G _{FS}	Forward Transconductance	3	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
2N5949	Through-Hole	TO-92	Bulk
SMP5949	Surface Mount	SOT23	Bulk
SMP5949TR	7" Tape and Reel: Max 3,000 Pieces 13" Tape and Reel: Max 9,000 Pieces	SOT23	Minimum 1,000 Pieces Tape and Reel
2N5949COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
2N5949CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

Maximum Ratings (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

Parameters	Value	Unit
V_{RGS} Reverse Gate Source and Gate Drain Voltage	30	V
I_{FG} Continuous Forward Gate Current	10	mA
P_D Continuous Device Power Dissipation	360	mW
P Power Derating		mW/ $^\circ\text{C}$
T_J Operating Junction Temperature	-55 to 125	$^\circ\text{C}$
T_{STG} Storage Temperature	-55 to 150	$^\circ\text{C}$

Static Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

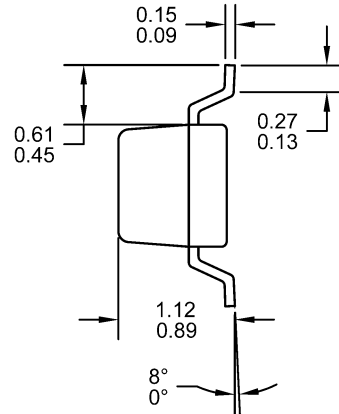
Parameters	Conditions	2N5949		Unit
		Min	Max	
$V_{(BR)GSS}$ Gate to Source Breakdown Voltage	$V_{DS} = 0V, I_G = 1\mu\text{A}$	-30		V
I_{GSS} Gate to Source Reverse Current	$V_{GS} = 15V, V_{DS} = 0V, T_A = 25^\circ\text{C}$ $V_{GS} = 15V, V_{DS} = 0V, T_A = 100^\circ\text{C}$		1	nA
$V_{GS(OFF)}$ Gate to Source Cutoff Voltage	$V_{DS} = 15V, I_D = 100\text{nA}$	-3	-7	V
V_{GS} Gate to Source Voltage	$V_{DS} = 15V, I_D = 1.2\text{mA}$	-2.25	-6.0	V
I_{DSS} Drain to Source Saturation Current	$V_{GS} = 0V, V_{DS} = 15V$ (Pulsed)	12	18	mA

Dynamic Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

Parameters	Conditions	2N5949		Unit
		Min	Max	
$R_{DS(ON)}$ Drain to Source ON Resistance	$V_{GS} = 0V, I_D = 0\text{mA}, f = 1\text{kHz}$		200	Ω
G_{FS} Forward Transconductance	$V_{DS} = 15V, V_{GS} = 0V, f = 100\text{MHz}$	3	7.5	mS
G_{OS} Output Conductance	$V_{DS} = 15V, V_{GS} = 0V, f = 100\text{MHz}$		150	μS
G_{IS} Input Conductance	$V_{DS} = 15V, V_{GS} = 0V, f = 100\text{MHz}$		250	μS
C_{iss} Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{MHz}$		6	pF
C_{rss} Reverse Transfer Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{MHz}$		2	pF
e_n Equivalent Circuit Input Noise Voltage	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{kHz}$		100	$\text{nV}/\sqrt{\text{Hz}}$

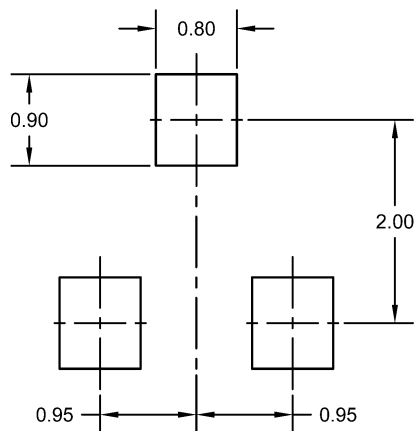
SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.12 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.